Units

Max

# **Electrical Characteristics** $T_J = 25^{\circ}C$ unless otherwise noted

**Parameter** 

Off Characteristics								
B <sub>VDSS</sub>	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V$	60	-	-	V		
Inee	Drain to Source Leakage Current	$V_{DS} = 60V$ , $T_{J} = 25^{\circ}C$	-	-	1	μА		

Test Conditions

Min

Тур

	B <sub>VDSS</sub>	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V$		60	-	-	V
	ı	Drain to Source Leakage Current	V <sub>DS</sub> =60V,	$T_J = 25^{\circ}C$	-	-	1	μΑ
IDSS	Diam to Source Leakage Current	$V_{GS} = 0V$	$T_J = 175^{\circ}C(Note 4)$	-	1	1	mA	
	I <sub>GSS</sub>	Gate to Source Leakage Current	$V_{GS} = \pm 20V$		-	-	±100	nA

## **On Characteristics**

Symbol

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$		1.0	1.9	3.0	V
		$I_D = 17.6A, T_J = 25^{\circ}C$	$T_{J} = 25^{\circ}C$	-	26	33	mΩ
r	Drain to Source On Resistance	V <sub>GS</sub> = 10V	$T_J = 175^{\circ}C(Note 4)$	) - 59	74	$m\Omega$	
r <sub>DS(on)</sub>	Diani to Source On Resistance	I <sub>D</sub> = 17.6A,	$T_{\rm J} = 25^{\rm o}{\rm C}$	-	34	42	$m\Omega$
		$V_{GS} = 4.5V$ $T_J = 175^{\circ}C(Note 4)$	-	74	90	mΩ	

# **Dynamic Characteristics**

C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V, f = 1MHz		-	878	-	pF
C <sub>oss</sub>	Output Capacitance			-	79	-	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			-	39	-	pF
$R_g$	Gate Resistance	f = 1MHz		-	2.4	-	Ω
$Q_{g(ToT)}$	Total Gate Charge at 10V	V <sub>GS</sub> = 0 to 10V	V <sub>DD</sub> = 48V	-	17	21	nC
Q <sub>g(th)</sub>	Threshold Gate Charge	V <sub>GS</sub> = 0 to 2V I <sub>D</sub> = 17.6A	-	8.3	10.5	nC	
$Q_{gs}$	Gate to Source Gate Charge		_	-	3	-	nC
$Q_{gd}$	Gate to Drain "Miller" Charge			ı	4	-	nC

# **Switching Characteristics**

t <sub>on</sub>	Turn-On Time	$V_{DD}$ = 30V, $I_{D}$ = 17.6A, $V_{GS}$ = 10V, $R_{GEN}$ = 6 $\Omega$	-	-	17	ns
t <sub>d(on)</sub>	Turn-On Delay Time		-	11	-	ns
t <sub>r</sub>	Rise Time		-	4	-	ns
t <sub>d(off)</sub>	Turn-Off Delay Time		-	31	-	ns
t <sub>f</sub>	Fall Time		-	4	-	ns
t <sub>off</sub>	Turn-Off Time		-	-	44	ns

## **Drain-Source Diode Characteristics**

$V_{SD}$	Source to Drain Diode Voltage	I <sub>SD</sub> = 17.6A, V <sub>GS</sub> = 0V	-	-	1.25	V
T <sub>rr</sub>	Reverse Recovery Time	$I_F = 17.6A$ , $dI_{SD}/dt = 100A/\mu s$ ,	-	25	38	ns
Q <sub>rr</sub>	Reverse Recovery Charge	V <sub>DD</sub> =48V	-	16.8	22	nC

## Notes:

4: The maximum value is specified by design at  $T_J$  = 175°C. Product is not tested to this condition in production.

# 

**Typical Characteristics** 

0.0

0

25

50

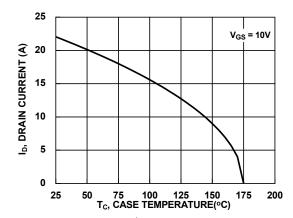


Figure 1. Normalized Power Dissipation vs Case Temperature

75

100

T<sub>C</sub>, CASE TEMPERATURE(°C)

125

150

175

Figure 2. Maximum Continuous Drain Current vs Case Temperature

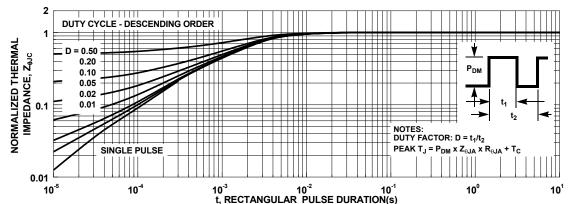


Figure 3. Normalized Maximum Transient Thermal Impedance

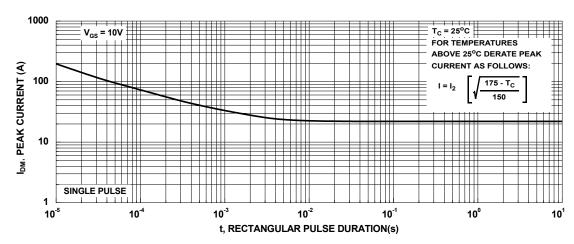


Figure 4. Peak Current Capability

# **Typical Characteristics**

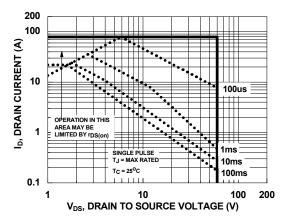
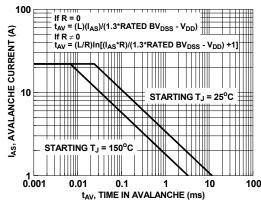


Figure 5. Forward Bias Safe Operating Area



NOTE: Refer to ON Semiconductor Application Notes AN7514 and AN7515

Figure 6. Unclamped Inductive Switching Capability

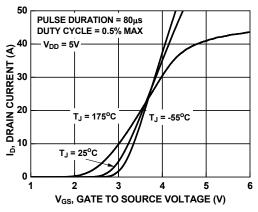


Figure 7. Transfer Characteristics

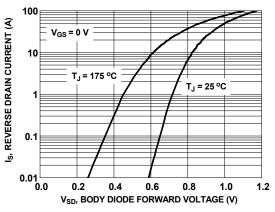


Figure 8. Forward Diode Characteristics

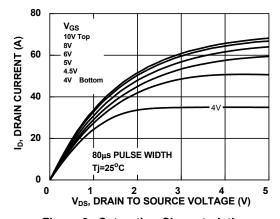


Figure 9. Saturation Characteristics

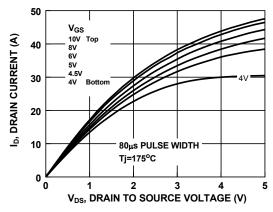


Figure 10. Saturation Characteristics

# **Typical Characteristics**

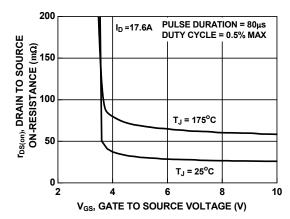


Figure 11. Rdson vs Gate Voltage

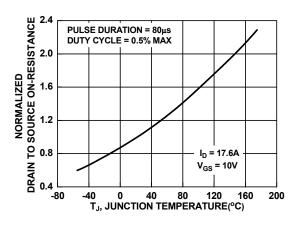


Figure 12. Normalized Rdson vs Junction Temperature

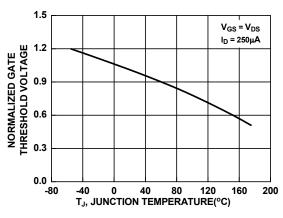


Figure 13. Normalized Gate Threshold Voltage vs
Temperature

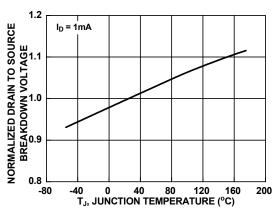


Figure 14. Normalized Drain to Source Breakdown Voltage vs Junction Temperature

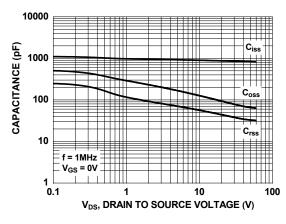


Figure 15. Capacitance vs Drain to Source Voltage

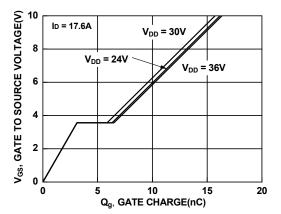


Figure 16. Gate Charge vs Gate to Source Voltage

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